

# Data Sheet

## Linear Field Sensors

### *KMY20, KMY21, KMZ20*

#### 中国

北京赛斯维测控技术有限公司

北京市朝阳区望京西路48号

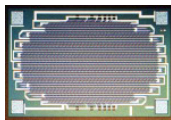
金隅国际C座1002

电话：+ 86 010 8477 5646

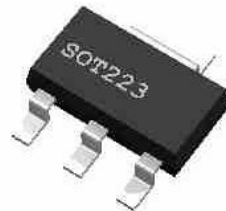
传真：+ 86 010 5894 9029

邮箱：[jangarmy@126.com](mailto:jangarmy@126.com)

FEATURES	APPLICATIONS
<ul style="list-style-type: none"> <li>• output proportional to magnetic field strength with very high sensitivity</li> <li>• very small hysteresis</li> <li>• large operating temperature range, from -40°C up to +150 °C</li> <li>• highly reliable</li> <li>• with / without internal magnet</li> </ul>	<ul style="list-style-type: none"> <li>• detection of very weak magnetic fields, like earth magnetic field, or field generated by small magnetic particles</li> <li>• detection of objects that distort non-local magnetic fields</li> <li>• revolution measurement on ferro-magnetic gears</li> <li>• contactless switch / displacement sensor</li> </ul>
DIES & PACKAGES	



dies **MR174B, MRHB**

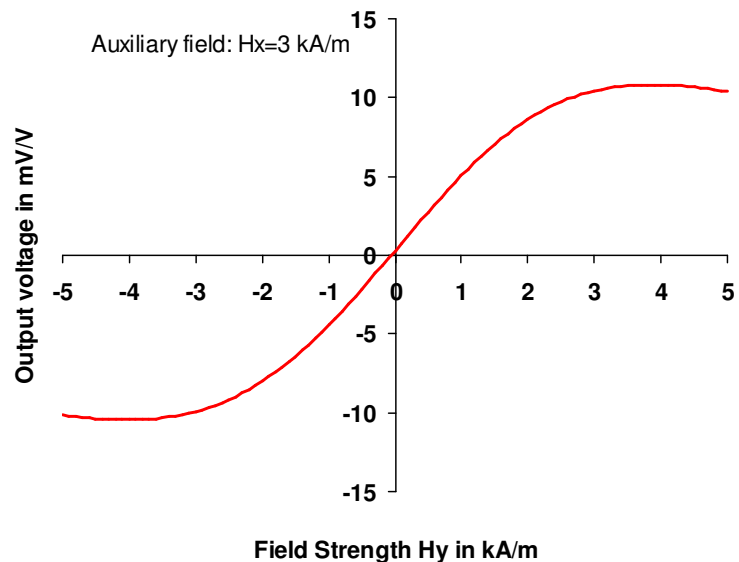
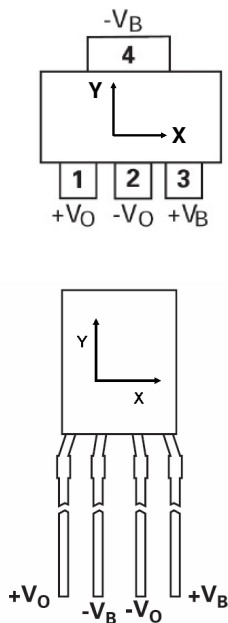


**KMY20M**



E-Line  
**KMZ20M**

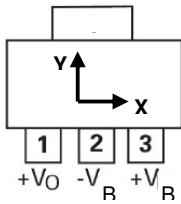
**KMY20 / KMZ20M**



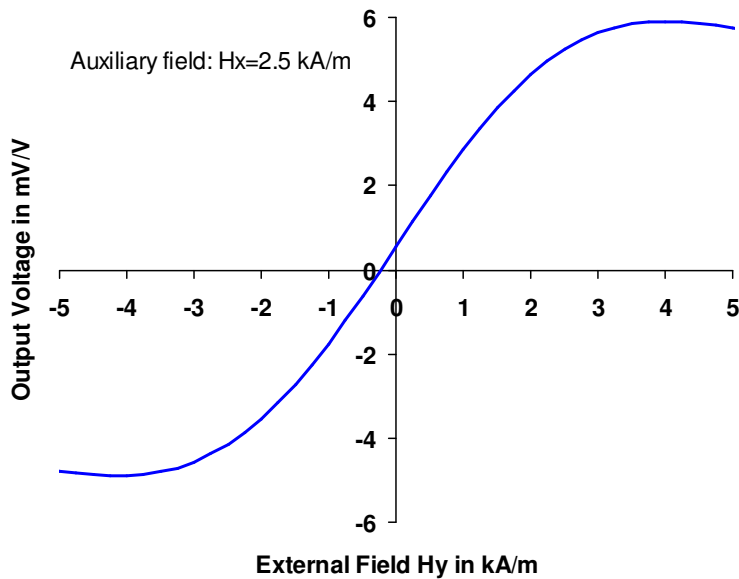
The **KMY** and **KMZ** sensors are highly sensitive magnetic field sensors which utilize the anisotropic magnetoresistance effect. The **KMY20** and **KMZ20** sensors contain a Wheatstone bridge.

**KMY21**

In contrast to the KMY20 sensor products, the **KMY21M** consists of a half bridge, making the sensor well suited for dynamic measurements.



It contains an internal magnet, which provides an auxiliary field of approx. 2.5 kA/m.



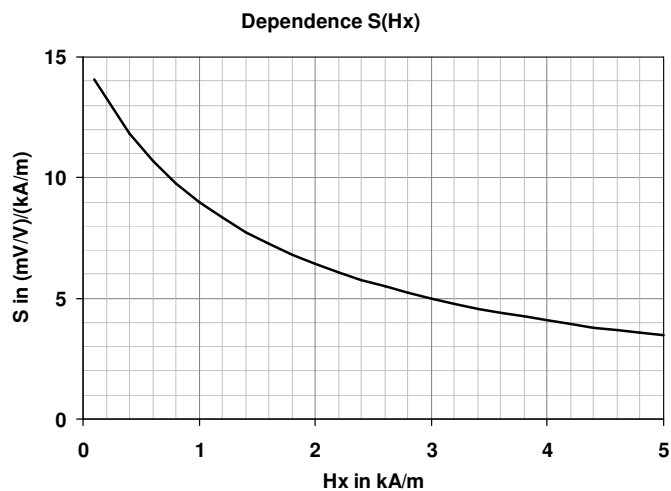
**GENERAL DESCRIPTION**

Due to its featured properties - high sensitivity and almost no hysteresis – the **KMY / KMZ** sensors are used in a wide range of applications, like magnetic field measurement, revolution counters, proximity detecting, position measurement.

An uniaxial linear magnetic field in y-direction will generate a linear output within the specified magnetic field range. The sensor is available in two types: the **KMY20 M** and **KMZ20 M** sensor types contain intrinsic magnets which provide an auxiliary magnetic field at the sensor die which prevents magnetic domains from flipping irregularly.

If the dies **MR174B** and **MRHB** or the **KMY20 S** are used, the auxiliary field has to be provided by the user. The dependence of the sensitivity with auxiliary field strength is depicted in the figure.

Auxiliary field strengths below  $H_x < 1.5$  kA/m are not recommended, as small disturbances may flip the magnetization domains. Sometimes, the magnetic conditions in the application may provide enough  $H_x$  bias field stabilization.



**CHARACTERISTIC VALUES**

PARAMETER	SYMBOL	CONDITION	MIN	TYP	MAX	UNIT
<b>Operating Limits</b>						
max. supply voltage	$V_{cc,max}$				10	V
max. current	$I_{cc,max}$	SOT223 E-Line			9	mA
operating temperature	$T_{op}$	SOT223, E-Line	-40		+150	°C
storage temperature	$T_{st}$	SOT223, E-Line	-40		+150	°C
<b>General Sensor Specifications</b>						
TC of amplitude	$TCSV$	Condition A, C	-0.36	-0.32	-0.28	%/K
TC of resistance	$TCBR$	Condition A, C	+0.27	+0.32	+0.37	%/K
TC of offset	$TCVoff$	Condition A, C	-4	0	+4	$\mu V/V/K$

<b>Sensor Specifications KMY20, KMZ20 (T=25 °C, Hx=3 kA/m)</b>						
PARAMETER	SYMBOL	CONDITION	MIN	TYP	MAX	UNIT
Supply voltage	$V_{cc}$	Condition A, B		5		V
Bridge resistance	$R_b$	Condition A, B	1200	1700	2200	$\Omega$
Output signal range	$\Delta V_o/V_{cc}$	Condition A, B	16	20	24	mV/V
Offset voltage	$V_{off}/V_{cc}$	Condition A, B	-1	0	+1	mV/V
Sensitivity	$S$	Condition A, B	3.7	4.7	5.7	mV/V/kA/m
Hysteresis	$V_H/V_{cc}$	Condition A, B	-	-	50	$\mu V/V$

<b>Sensor Specifications KMY21M (T=25 °C, Hx=2.5 kA/m)</b>						
PARAMETER	SYMBOL	CONDITION	MIN	TYP	MAX	UNIT
Supply voltage	$V_{cc}$	Condition A, B		5		V
Bridge resistance	$R_b$	Condition A, B	1100	1500	1900	$\Omega$
Output signal range	$\Delta V_o/V_{cc}$	Condition A, B	8	9.5	12	mV/V
Offset voltage	$V_{off}/V_{cc}$	Condition A, B	48	50	52	%Vcc
Sensitivity	$S$	Condition A, B	2.05	2.50	3.10	mV/V/kA/m
Hysteresis	$V_H/V_{cc}$	Condition A, B	-	-	50	$\mu V/V$

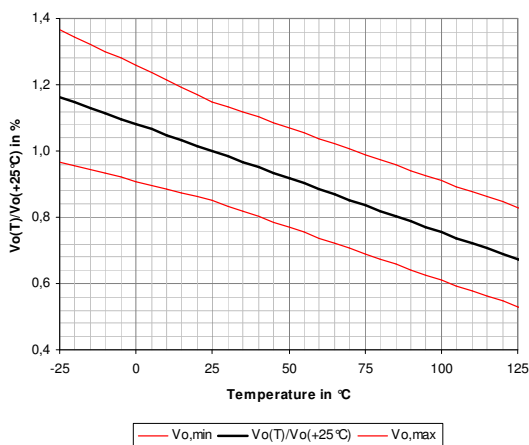
Stress above one or more of the limiting values may cause permanent damage to the device. Exposure to limiting values for extended periods may affect device reliability.

**MEASUREMENT CONDITIONS**

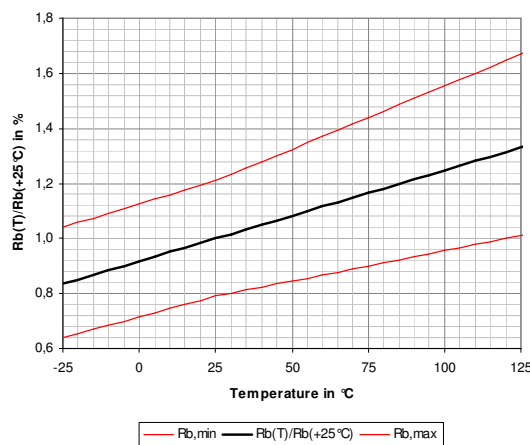
PARAMETER	SYMBOL	UNIT	CONDITION
<b>Condition A: Set Up Conditions</b>			
Ambient temperature	T	°C	23±5
Supply voltage	V <sub>cc</sub>	V	5
Output voltage	V <sub>O</sub>	mV	V <sub>O</sub> =(V <sub>O+</sub> -V <sub>O-</sub> )
	V <sub>O</sub> /V <sub>cc</sub>	mV/V	output voltages are also given independently on supply voltage: example: V <sub>O</sub> /V <sub>cc</sub> =(V <sub>O+</sub> -V <sub>O-</sub> )/V <sub>cc</sub>
Reference half bridge			measure MR half bridge against reference half bridge 2* 2 kΩ 0.1%
<b>for full bridge sensors (KMY20S, KMY20M, KMZ20S, KMZ20M)</b>		<b>for half bridge sensors (KMY21M)</b>	
<i>The output voltage of the MR half bridge is measured against a reference half bridge</i>			
<b>Condition B: Sensor Specifications (T=23±5 °C, H<sub>x</sub>=3.0±0.5 kA/m)</b>			
Output voltage range	ΔV <sub>O</sub> /V <sub>cc</sub>	mV/V	H <sub>y</sub> = -7...+7 kA/m; ΔV <sub>O</sub> = (V <sub>O,max</sub> - V <sub>O,min</sub> )
Offset voltage	V <sub>off</sub> /V <sub>cc</sub>	mV/V	H <sub>y</sub> = 0; V <sub>off</sub> = V <sub>O</sub> (H <sub>y</sub> )
Sensitivity	S	(mV/V)/(kA/m)	H <sub>y</sub> = 1kA/m; S := $\frac{V_0(+H_y) - V_0(-H_y)}{2 \cdot V_{cc}}$
Hysteresis	V <sub>H</sub> /V <sub>cc</sub>	μV/V	H <sub>y</sub> in kA/m (V <sub>O</sub> (H <sub>y</sub> = 0; H <sub>y</sub> = -1 → +1) - V <sub>O</sub> (H <sub>y</sub> = 0; H <sub>y</sub> = +1 → -1))/V <sub>cc</sub>

PARAMETER	SYMBOL	UNIT	CONDITION
<b>C. Sensor Specifications (T=-25 °C, +125 °C)</b>			
Ambient temperatures	T	°C	T <sub>1</sub> =-25 °C, T <sub>0</sub> =+25 °C, T <sub>2</sub> =+125 °C
TC of amplitude	TCSV	%/K	$TCV = \frac{1}{(T_2 - T_1)} \cdot \frac{\Delta V_0 / V_{cc}(T_2) - \Delta V_0 / V_{cc}(T_1)}{\Delta V_0 / V_{cc}(T_1)} \cdot 100\%$
TC of resistance	TCBR	%/K	$TCR = \frac{1}{(T_2 - T_1)} \cdot \frac{R(T_2) - R(T_1)}{R(T_1)} \cdot 100\%$
TC of offset	TCVoff	(μV/V)/K	$TCVoff = \frac{V_{off}(T_2) - V_{off}(T_1)}{(T_2 - T_1)}$

**TEMPERATURE DEPENDENCIES**



*signal amplitude related to room temperature value*



*bridge resistance related to room temperature value*

**LEGAL DISCLAIMER**

This product is not designed for use in life support appliances, devices or systems where malfunction of this product can reasonably be expected to result in personal injury. HL Planartechnik GmbH customers using or selling this product for use in such applications do so at their own risk and agree to fully indemnify HL Planartechnik GmbH for any damages resulting from such improper use or sale.

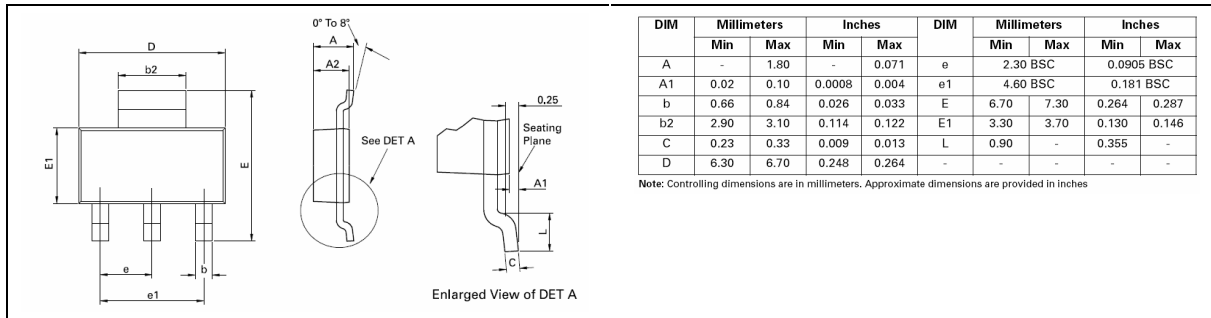
This data sheet contains target specifications for product development which may be subject to changes without notice.

**PACKAGES**

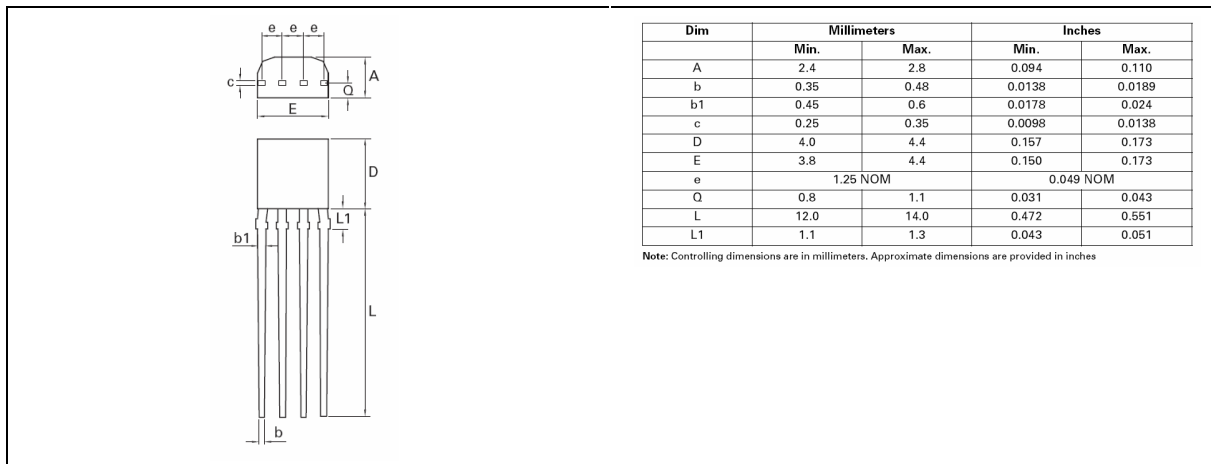
**DIE LAYOUT**

Die layout and dimensions on request.

**SOT223**



**E-LINE 4 PIN**



**ORDERING**

DEVICE	DIE	PACKAGE	INTERNAL MAGNET	PART NUMBER
MR174B	full bridge	wafer	n/a	G-MRCH-002
MRHB	half bridge	wafer	n/a	G-MRCH-009
KMY 20 S	full bridge	SOT-223	NO	G-MRCH-006
KMY 20 M	full bridge	SOT-223	YES	G-MRCH-001
KMY 21 M	half bridge	SOT-223	YES	G-MRCH-011
KMZ 20 S	full bridge	E-Line	NO	G-MRCH-007
KMZ 20 M	full bridge	E-Line	YES	G-MRCH-003